

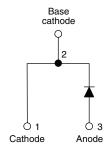
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Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



TO-247AC 2L



PRIMARY CHARACTERISTICS				
I _{F(AV)}	8 A			
V_{R}	600 V			
V _F at I _F	1.4 V			
t _{rr} typ.	18 ns			
T _J max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



COMPLIANT HALOGEN

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA08PB60... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the to portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_R		600	V	
Maximum continuous forward current	I _F	T _C = 100 °C	8		
Single pulse forward current	I _{FSM}	t _p = 10 ms	60	А	
Maximum repetitive forward current	I _{FRM}		24		
Maximum power dissipation	P _D	T _C = 25 °C	36	- w	
Maximum power dissipation		T _C = 100 °C	14		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
		I _F = 8.0 A	See fig. 1	-	1.4	1.7	V
Maximum forward voltage	V_{FM}	I _F = 16 A		-	1.7	2.1	
		I _F = 8.0 A, T _J = 125 °C		-	1.4	1.7	
Maximum reverse		V _R = V _R rated	Coofie 0	=	0.3	5.0	
leakage current		$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2		100	500	- μΑ
Junction capacitance	C _T	V _R = 200 V See fig. 3		=	10	25	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 - nH		nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	18	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	37	55	ns
000 lig. 0, 10	t _{rr2} T _J = 125 °C	-	55	90			
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	3.5	5.0	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	4.5	8.0	A
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138	nC
See fig. 7	Q _{rr2}	T _J = 125 °C		-	124	360	IIC
Peak rate of fall of recovery	3 GI(rec)M/GET 1J = 23 G	-	240	-	Δ /		
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	210	-	- A/μs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	$R_{ heta JC}$		-	-	3.5	
Thermal resistance, junction to ambient	$R_{\theta JA}$	Typical socket mount	-	-	40	K/W
Thermal resistance, case to heatsink	R _{ecs}	Mounting surface, flat, smooth, and greased -		0.25	-	
Weight			-	6.0	-	g
vveignt			-	0.21	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA08PB60			

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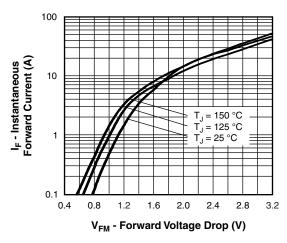


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

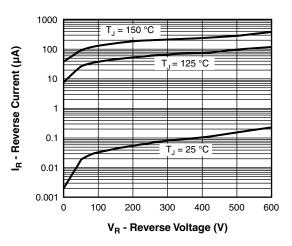


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

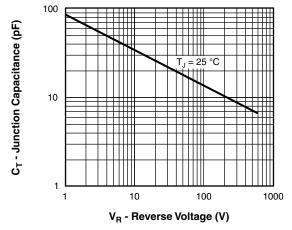


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

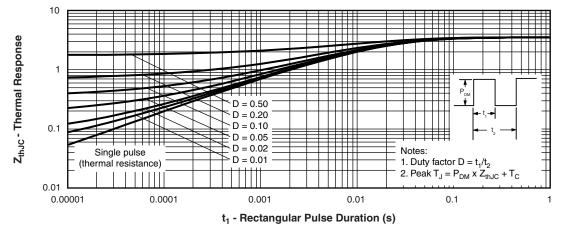


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Revision: 29-Nov-2019 3 Document Number: 94041 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u>

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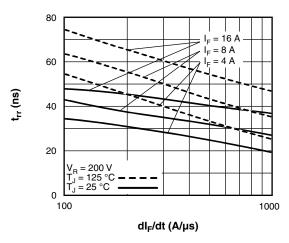


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

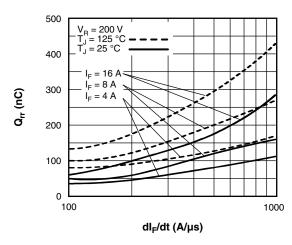


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

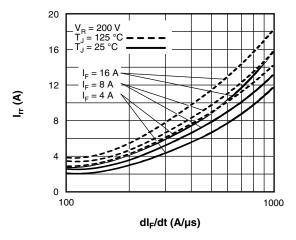


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

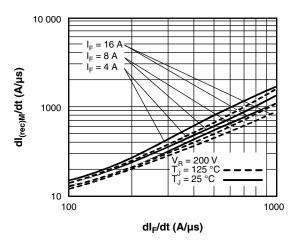
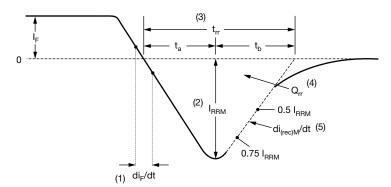


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- $\begin{array}{l} \text{(3) } t_{rr} \text{ reverse recovery time measured} \\ \text{from zero crossing point of negative} \\ \text{going } I_{r} \text{ to point where a line passing} \\ \text{through 0.75 } I_{RRM} \text{ and 0.50 } I_{RRM} \\ \text{extrapolated to zero current.} \end{array}$
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

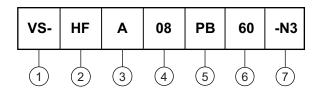
Fig. 9 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

- Electron irradiated

- Current rating (08 = 8A)

5 - PB = TO-247AC, 2 pins

6 - Voltage rating: (60 = 600 V)

7 - Environmental digit:

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFO	RMATION (Example)		
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-HFA08PB60-N3	25	500	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96144</u>				
Part marking information	www.vishay.com/doc?95648			

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